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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Discontinued at Digi-Key
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	34
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	20K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 10x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LFQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101gjdfb-30

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 1-1. List of Ordering Part Numbers

(9/12)

Pin count	Package	Data flash	Fields of Application	Ordering Part Number
64 pins	64-pin plastic LFQFP (10 × 10 mm, 0.5 mm pitch)	Mounted	A	R5F100LCAFB#V0, R5F100LDAFB#V0, R5F100LEAFB#V0, R5F100LFAFB#V0, R5F100LGAFB#V0, R5F100LHAFB#V0, R5F100LJAFB#V0, R5F100LKAFB#V0, R5F100LCAFB#X0, R5F100LDAFB#X0, R5F100LEAFB#X0, R5F100LFAFB#X0, R5F100LFAFB#X0, R5F100LJAFB#X0, R5F100LJAFB#X0, R5F100LJAFB#X0, R5F100LJAFB#X0, R5F100LJAFB#X0, R5F100LLAFB#X0
			D	R5F100LCDFB#V0, R5F100LDDFB#V0, R5F100LEDFB#V0, R5F100LFDFB#V0, R5F100LFDFB#V0, R5F100LHDFB#V0, R5F100LJDFB#V0, R5F100LJDFB#V0, R5F100LDFB#V0 R5F100LCDFB#X0, R5F100LDDFB#X0, R5F100LEDFB#X0, R5F100LFDFB#X0, R5F100LFDFB#X0, R5F100LJDFB#X0, R5F100LJDFB#X0, R5F100LJDFB#X0, R5F100LLDFB#X0
			G	R5F100LCGFB#V0, R5F100LDGFB#V0, R5F100LEGFB#V0, R5F100LFGFB#V0 R5F100LCGFB#X0, R5F100LDGFB#X0, R5F100LEGFB#X0, R5F100LFGFB#X0 R5F100LGGFB#V0, R5F100LHGFB#V0, R5F100LJGFB#V0
				R5F100LGGFB#X0, R5F100LHGFB#X0, R5F100LJGFB#X0
		Not mounted	A	R5F101LCAFB#V0, R5F101LDAFB#V0, R5F101LEAFB#V0, R5F101LFAFB#V0, R5F101LGAFB#V0, R5F101LHAFB#V0, R5F101LJAFB#V0, R5F101LKAFB#V0, R5F101LCAFB#X0, R5F101LDAFB#X0, R5F101LEAFB#X0,
			D	R5F101LFAFB#X0, R5F101LGAFB#X0, R5F101LHAFB#X0, R5F101LJAFB#X0, R5F101LKAFB#X0, R5F101LLAFB#X0 R5F101LCDFB#V0, R5F101LDDFB#V0, R5F101LEDFB#V0, R5F101LFDFB#V0, R5F101LFDFB#V0, R5F101LJDFB#V0, R5F101LLDFB#V0 R5F101LCDFB#X0,
				R5F101LFDFB#X0, R5F101LGDFB#X0, R5F101LHDFB#X0, R5F101LJDFB#X0, R5F101LKDFB#X0, R5F101LLDFB#X0
	64-pin plastic VFBGA (4 × 4 mm, 0.4 mm pitch)	Mounted	A	R5F100LCABG#U0, R5F100LDABG#U0, R5F100LEABG#U0, R5F100LFABG#U0, R5F100LGABG#U0, R5F100LHABG#U0, R5F100LJABG#U0 R5F100LCABG#W0, R5F100LDABG#W0, R5F100LEABG#W0,
	picity		G	R5F100LFABG#W0, R5F100LGABG#W0, R5F100LHABG#W0, R5F100LJABG#W0 R5F100LCGBG#U0, R5F100LDGBG#U0, R5F100LEGBG#U0, R5F100LFGBG#U0, R5F100LGGBG#U0, R5F100LHGBG#U0, R5F100LJGBG#U0
				R5F100LCGBG#W0, R5F100LDGBG#W0, R5F100LEGBG#W0, R5F100LFGBG#W0, R5F100LGGBG#W0, R5F100LHGBG#W0, R5F100LJGBG#W0
		Not mounted	A	R5F101LCABG#U0, R5F101LDABG#U0, R5F101LEABG#U0, R5F101LFABG#U0, R5F101LGABG#U0, R5F101LHABG#U0, R5F101LJABG#U0 R5F101LCABG#W0, R5F101LCABG#W0, R5F101LEABG#W0,
				R5F101LFABG#W0, R5F101LGABG#W0, R5F101LHABG#W0, R5F101LJABG#W0

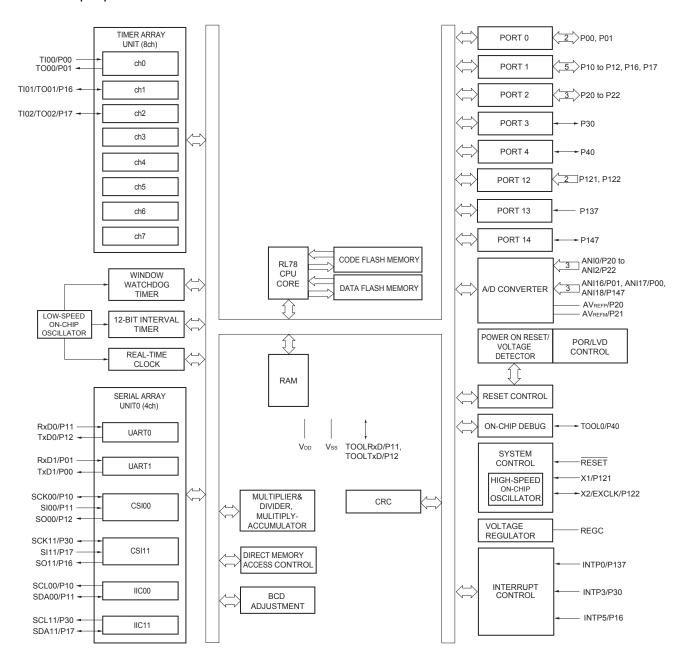
Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

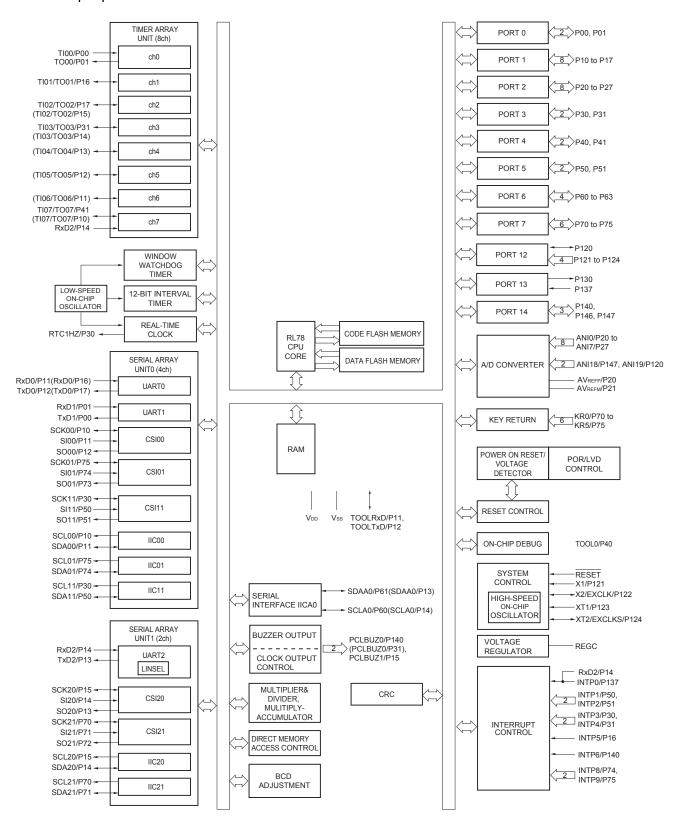


1.5 Block Diagram

1.5.1 20-pin products

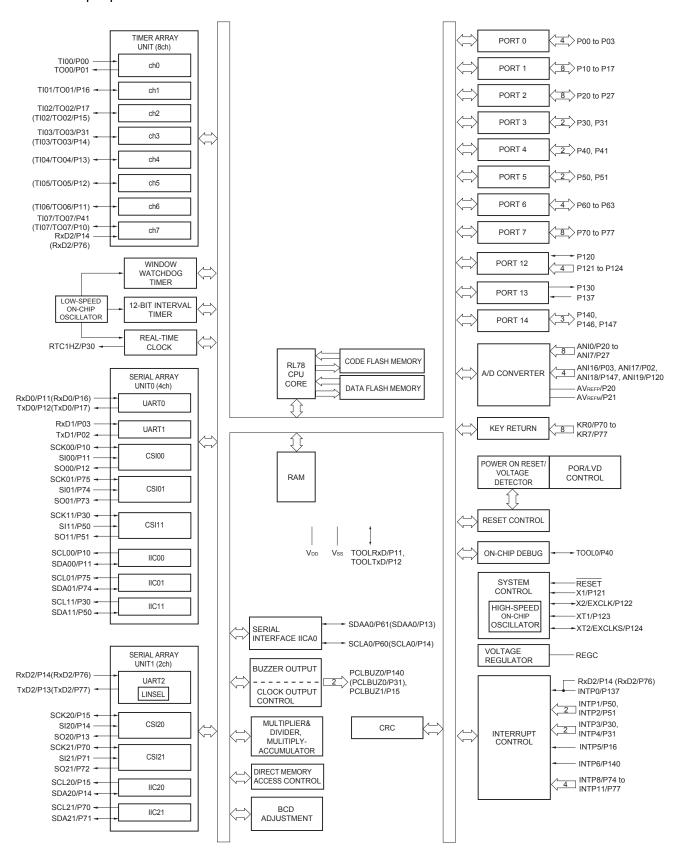


1.5.9 48-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.5.10 52-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V) (5/5)

Items	Symbol	Conditio	ns		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ішн1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vi = EVDDO	Vi = EVDD0			1	μΑ
	ILIH2	P20 to P27, P1 <u>37,</u> P150 to P156, RESET	$V_I = V_{DD}$				1	μΑ
	Ішнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μΑ
				In resonator connection			10	μΑ
Input leakage current, low	lut1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	VI = EVsso				-1	μΑ
	ILIL2	P20 to P27, P137, P150 to P156, RESET	Vı = Vss				-1	μΑ
	LIL3	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
On-chip pll-up resistance	R∪	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vı = EVsso	, In input port	10	20	100	kΩ

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz

 $2.4~V \le V_{DD} \le 5.5~V @ 1~MHz$ to 16~MHz

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 8 MHz LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fih: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT	HS (high-	$f_{IH} = 32 \text{ MHz}^{Note 4}$	V _{DD} = 5.0 V		0.54	1.63	mA
current	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.54	1.63	mA
				$f_{IH} = 24 \text{ MHz}^{\text{Note 4}}$	V _{DD} = 5.0 V		0.44	1.28	mA
					V _{DD} = 3.0 V		0.44	1.28	mA
				fih = 16 MHz Note 4	V _{DD} = 5.0 V		0.40	1.00	mA
					V _{DD} = 3.0 V		0.40	1.00	mA
			LS (low-	fih = 8 MHz Note 4	V _{DD} = 3.0 V		260	530	μА
			speed main) mode Note 7		V _{DD} = 2.0 V		260	530	μА
			LV (low-	f _{IH} = 4 MHz ^{Note 4}	V _{DD} = 3.0 V		420	640	μA
			voltage main) mode		V _{DD} = 2.0 V		420	640	μА
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.28	1.00	mA
			speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.45	1.17	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.28	1.00	mA
				V _{DD} = 3.0 V	Resonator connection		0.45	1.17	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.19	0.60	mA
				$V_{DD} = 5.0 \text{ V}$	Resonator connection		0.26	0.67	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.19	0.60	mA
				$V_{DD} = 3.0 \text{ V}$	Resonator connection		0.26	0.67	mA
			LS (low-	$f_{MX} = 8 MHz^{Note 3}$	Square wave input		95	330	μΑ
			speed main) mode Note 7	V _{DD} = 3.0 V	Resonator connection		145	380	μΑ
				$f_{MX} = 8 MHz^{Note 3}$	Square wave input		95	330	μΑ
				$V_{DD} = 2.0 \text{ V}$	Resonator connection		145	380	μΑ
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.25	0.57	μΑ
			clock	T _A = -40°C	Resonator connection		0.44	0.76	μΑ
			operation	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.30	0.57	μΑ
				T _A = +25°C	Resonator connection		0.49	0.76	μΑ
				$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$	Square wave input		0.37	1.17	μΑ
				T _A = +50°C	Resonator connection		0.56	1.36	μΑ
				$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$	Square wave input		0.53	1.97	μΑ
				T _A = +70°C	Resonator connection		0.72	2.16	μA
				$f_{SUB} = 32.768 \text{ kHz}^{Note 5}$	Square wave input		0.82	3.37	μΑ
				T _A = +85°C	Resonator connection		1.01	3.56	μΑ
	IDD3 Note 6	STOP	T _A = -40°C				0.18	0.50	μΑ
		mode ^{Note 8}	T _A = +25°C				0.23	0.50	μА
			T _A = +50°C				0.30	1.10	μА
			T _A = +70°C				0.46	1.90	μА
			T _A = +85°C				0.75	3.30	μΑ

(Notes and Remarks are listed on the next page.)



(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT	HS (high-	f _{IH} = 32 MHz ^{Note 4}	V _{DD} = 5.0 V		0.62	1.89	mA
current	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.62	1.89	mA
			mode	fih = 24 MHz Note 4	V _{DD} = 5.0 V		0.50	1.48	mA
					V _{DD} = 3.0 V		0.50	1.48	mA
				fih = 16 MHz Note 4	V _{DD} = 5.0 V		0.44	1.12	mA
					V _{DD} = 3.0 V		0.44	1.12	mA
			LS (low-	fih = 8 MHz Note 4	V _{DD} = 3.0 V		290	620	μΑ
			speed main) mode Note 7		V _{DD} = 2.0 V		290	620	μΑ
			LV (low-	fih = 4 MHz Note 4	V _{DD} = 3.0 V		460	700	μΑ
			voltage main) mode Note 7		V _{DD} = 2.0 V		460	700	μΑ
				fmx = 20 MHz ^{Note 3} ,	Square wave input		0.31	1.14	mA
			speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.48	1.34	mA
				$f_{MX} = 20 \text{ MHz}^{Note 3},$	Square wave input		0.31	1.14	mA
				V _{DD} = 3.0 V	Resonator connection		0.48	1.34	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.21	0.68	mA
				V _{DD} = 5.0 V	Resonator connection		0.28	0.76	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.21	0.68	mA
				V _{DD} = 3.0 V	Resonator connection		0.28	0.76	mA
			LS (low- speed main) mode Note 7	$f_{MX} = 8 MHz^{Note 3}$	Square wave input		110	390	μΑ
				V _{DD} = 3.0 V	Resonator connection		160	450	μΑ
				$f_{MX} = 8 MHz^{Note 3},$	Square wave input		110	390	μΑ
				V _{DD} = 2.0 V	Resonator connection		160	450	μΑ
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.31	0.66	μΑ
			clock operation	T _A = -40°C	Resonator connection		0.50	0.85	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.38	0.66	μΑ
				T _A = +25°C	Resonator connection		0.57	0.85	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.47	3.49	μΑ
				T _A = +50°C	Resonator connection		0.66	3.68	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.80	6.10	μΑ
				T _A = +70°C	Resonator connection		0.99	6.29	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		1.52	10.46	μΑ
				T _A = +85°C	Resonator connection		1.71	10.65	μΑ
	IDD3 Note 6	STOP mode ^{Note 8}	T _A = -40°C				0.19	0.54	μΑ
		mode	T _A = +25°C				0.26	0.54	μΑ
		<u></u>	T _A = +50°C				0.35	3.37	μΑ
			T _A = +70°C				0.68	5.98	μA
			T _A = +85°C				1.40	10.34	μΑ

(Notes and Remarks are listed on the next page.)



3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DD0} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

$$\label{eq:maximum transfer rate} \text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \ln{(1-\frac{2.0}{V_b})}\} \times 3} \text{ [bps]}$$

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.0}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- 5. Use it with $EV_{DD0} \ge V_b$.
- **6.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V \leq EV_{DD0} < 3.3 V and 1.6 V \leq V_b \leq 2.0 V

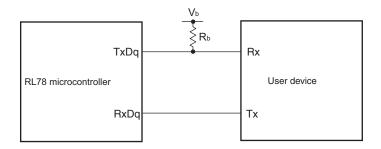
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln \ (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **7.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.

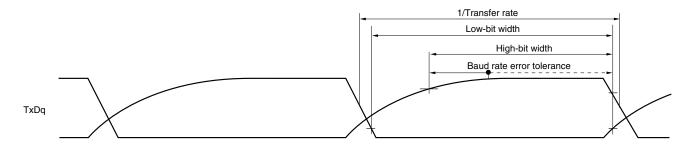
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

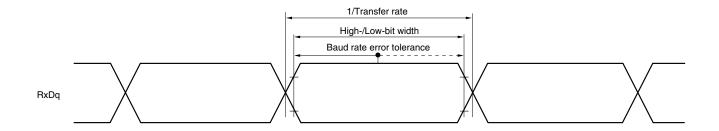
UART mode connection diagram (during communication at different potential)





UART mode bit width (during communication at different potential) (reference)





- $\begin{tabular}{ll} \begin{tabular}{ll} \bf R_b[\Omega]: Communication line (TxDq) pull-up resistance, \\ C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage \\ \end{tabular}$
 - 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (1/2)

(Ta = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	, -	h-speed Mode	,	v-speed Mode	,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$\begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned}$		1000 Note 1		300 Note 1		300 Note 1	kHz
		$\label{eq:section} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$		1000 Note 1		300 Note 1		300 Note 1	kHz
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $		400 Note 1		300 Note 1		300 Note 1	kHz
		$\label{eq:section} \begin{split} 2.7 \ V & \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$		400 Note 1		300 Note 1		300 ote 1	kHz
		$\begin{split} &1.8~V \leq EV_{DD0} < 3.3~V,\\ &1.6~V \leq V_b \leq 2.0~V^{\text{Note 2}},\\ &C_b = 100~pF,~R_b = 5.5~k\Omega \end{split}$		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr tLow = "L"	tLOW	$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 50 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	475		1550		1550		ns
		eq:second-seco	475		1550		1550		ns
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $	1150		1550		1550		ns
		$\label{eq:section} \begin{split} 2.7 \ V & \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V & \leq V_b \leq 2.7 \ V, \\ C_b & = 100 \ pF, \ R_b = 2.7 \ k\Omega \end{split}$	1150		1550		1550		ns
		$\begin{split} &1.8~V \leq EV_{DD0} < 3.3~V,\\ &1.6~V \leq V_b \leq 2.0~V^{\text{Note 2}},\\ &C_b = 100~pF,~R_b = 5.5~k\Omega \end{split}$	1550		1550		1550		ns
Hold time when SCLr = "H"	tнівн	$ 4.0 \ V \le EV_{DD0} \le 5.5 \ V, $ $ 2.7 \ V \le V_b \le 4.0 \ V, $ $ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega $	245		610		610		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 50 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $	200		610		610		ns
		$ \begin{aligned} & 4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ & 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ & C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned} $	675		610		610		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $	600		610		610		ns
		$\begin{split} &1.8~V \leq EV_{DDO} < 3.3~V,\\ &1.6~V \leq V_b \leq 2.0~V^{\text{Note 2}},\\ &C_b = 100~pF,~R_b = 5.5~k\Omega \end{split}$	610		610		610		ns

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

<R>

2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$



(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{\text{DD}0} = \text{EV}_{\text{DD}1} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS}0} = \text{EV}_{\text{SS}1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{\text{DD}}, \text{Reference voltage (-)} = \text{V}_{\text{SS}})$

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$		1.2	±7.0	LSB
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3		1.2	±10.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI0 to ANI14,	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
		ANI16 to ANI26	$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μS
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μS
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
		Target pin: Internal	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μS
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±0.85	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±0.85	%FSR
Integral linearity errorNote 1	ILE	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±4.0	LSB
			$1.6~V \leq V_{DD} \leq 5.5~V$ Note 3			±6.5	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$1.8~V \leq V_{DD} \leq 5.5~V$			±2.0	LSB
			$1.6~\text{V} \leq \text{VDD} \leq 5.5~\text{V}$ Note 3			±2.5	LSB
Analog input voltage	Vain	ANI0 to ANI14		0		V _{DD}	٧
		ANI16 to ANI26		0		EV _{DD0}	٧
		Internal reference voltage (2.4 V ≤ VDD ≤ 5.5 V, HS (hi	gh-speed main) mode)		V _{BGR} Note 4		V
		Temperature sensor output (2.4 V ≤ VDD ≤ 5.5 V, HS (hi	-		VTMPS25 Note 4	1	V

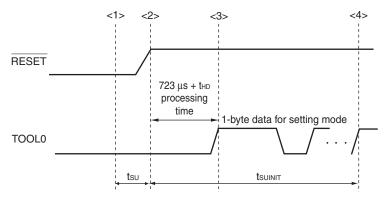
Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When the conversion time is set to 57 μ s (min.) and 95 μ s (max.).
- 4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

2.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuіліт	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μS
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

tsu: Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

3.3 DC Characteristics

3.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	2.4 V ≤ EV _{DD0} ≤ 5.5 V			-3.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	$4.0~V \leq EV_{DD0} \leq 5.5~V$			-30.0	mA
		P125 to P127, P130, P140 to P145 (When duty ≤ 70% Note 3) Total of P05, P06, P10 to P17, P30, P31, 4 P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to	$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V}$			-10.0	mA
			$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			-5.0	mA
						-30.0	mA
			$2.7~V \leq EV_{DD0} < 4.0~V$			-19.0	mA
			2.4 V ≤ EVDD0 < 2.7 V			-10.0	mA
		Total of all pins (When duty $\leq 70\%^{\text{Note 3}}$)	$2.4~V \le EV_{DD0} \le 5.5~V$			-60.0	mA
Іон2		Per pin for P20 to P27, P150 to P156	$2,4~V \leq V_{DD} \leq 5.5~V$			-0.1 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	$2.4~V \leq V_{DD} \leq 5.5~V$			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.
 - 2. Do not exceed the total current value.
 - **3.** Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(IOH \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and $I_{OH} = -10.0$ mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \cong -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 32 MHz $2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 16 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Condit	ions	HS (high-spee	ed main) Mode	Unit	
					MIN.	MAX.		
Transfer rate		Transmission	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$			Note 1	bps	
			$2.7~V \leq V_b \leq 4.0~V$	$2.7~V \leq V_b \leq 4.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \ pF, \ R_b = 1.4 \ k\Omega, \ V_b = 2.7 \ V$		2.6 Note 2	Mbps
			$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0$			Note 3	bps	
	V,	$V,$ $2.3~V \leq V_b \leq 2.7~V$	Theoretical value of the maximum transfer rate $C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega, \ V_b = 2.3 \ V$		1.2 Note 4	Mbps		
			2.4 V ≤ EV _{DD0} < 3.3			Note 5	bps	
		$V,$ $1.6~V \leq V_b \leq 2.0~V$	Theoretical value of the maximum transfer rate $C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 V$		0.43 Note 6	Mbps		

Notes 1. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV_{DD0} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.2}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DDO} < 4.0 V and 2.4 V \leq V_b \leq 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

$$\text{Baud rate error (theoretical value)} = \frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{2.0}{V_b})}\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.



3.5.2 Serial interface IICA

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (h	igh-spee	ed main)	Mode	Unit
				ndard ode	Fast	Mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fclk ≥ 3.5 MHz	-	_	0	400	kHz
		Standard mode: fcLK ≥ 1 MHz	0	100	ı	_	kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μS
Hold time ^{Note 1}	thd:sta		4.0		0.6		μS
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μS
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μS
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	0.9	μS
Setup time of stop condition	tsu:sto		4.0		0.6		μS
Bus-free time	tBUF		4.7		1.3		μS

Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.

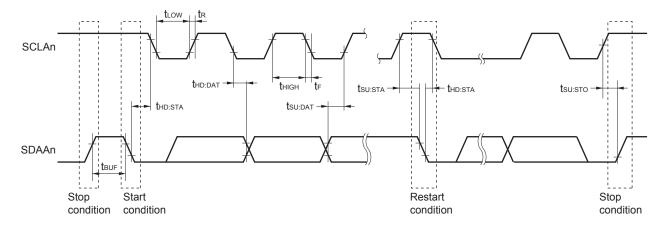
2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



Remark n = 0, 1

<R>

(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions	s	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall errorNote 1	AINL	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target pin: ANI0 to ANI14,	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
		ANI16 to ANI26	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
		Target pin: Internal reference 2	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μS
			$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μS
		sensor output voltage (HS	$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
		(high-speed main) mode)					
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±4.0	LSB
Differential linearity error	DLE	10-bit resolution	$2.4~\text{V} \leq \text{Vdd} \leq 5.5~\text{V}$			±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI14		0		V _{DD}	V
		ANI16 to ANI26		0		EV _{DD0}	V
		Internal reference voltage outpotential (2.4 V \leq VDD \leq 5.5 V, HS (high-		VBGR Note 3		V	
		Temperature sensor output vo $(2.4 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, HS (high-$	· ·	VTMPS25 Note 3			V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

4.7 40-pin Products

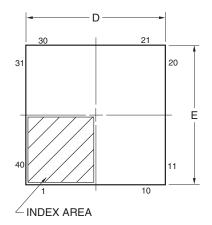
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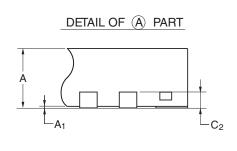
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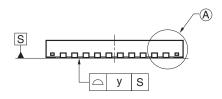
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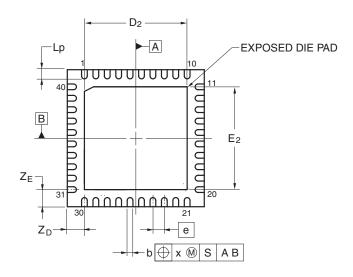
JEITA Package code	RENESAS code	Previous code	MASS (TYP.) [g]
P-HWQFN40-6x6-0.50	PWQN0040KC-A	P40K8-50-4B4-5	0.09











Referance Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	5.95	6.00	6.05
E	5.95	6.00	6.05
А			0.80
A ₁	0.00		
b	0.18	0.25	0.30
е		0.50	_
Lp	0.30	0.40	0.50
х			0.05
у			0.05
Z _D		0.75	_
Z _E		0.75	
C ₂	0.15	0.20	0.25
D ₂		4.50	
E ₂	_	4.50	

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